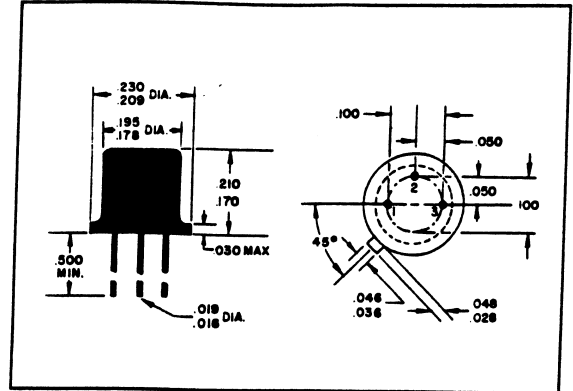


**NPN SILICON PLANEX*
 TRANSISTOR**

**2N2483
 2N2484**

2N2483 and 2N2484 are silicon NPN PLANEX* transistors designed especially for low noise, low level, high gain amplifier applications. They are manufactured in accordance with the



MECHANICAL DATA

CASE: JEDEC TO-18
 TERMINAL CONNECTIONS:
 Lead 1 Emitter
 Lead 2 Base
 Lead 3 Collector (Electrically connected to case)

ELECTRICAL DATA

ABSOLUTE MAXIMUM RATINGS:

Collector to Base Voltage V_{CBO}	60 volts
Collector to Emitter Voltage V_{CEO}	60 volts
Emitter to Base Voltage V_{EBO}	6.0 volts
Total Device Dissipation	
@ Case Temperature 25° C	1.2 watts
@ Case Temperature 100° C	0.68 watts
@ Free Air Temperature 25° C	0.36 watts
Junction Temperature (Operating)	-65° C to +200° C
Storage Temperature	-65° C to +300° C

ELECTRICAL CHARACTERISTICS: @ 25° C (unless otherwise noted)

	SYM.	CONDITIONS	2N2483 MIN.	2N2483 MAX.	2N2484 MIN.	2N2484 MAX.	UNITS
Collector to Base Breakdown Voltage	BV_{CBO}	$I_C=10 \mu A$	60	60	volts
Collector to Emitter Breakdown Voltage	BV_{CEO}	$I_C=10 mA \blacktriangle$	60	60	volts
Emitter to Base Breakdown Voltage	BV_{EBO}	$I_E=10 \mu A$	6.0	6.0	volts
Collector Cutoff Current	I_{CBO1}	$V_{CB}=45 V$	10	10	nA
	I_{CBO2}	$V_{CB}=45 V, TA=150^\circ C$	10	10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5.0 V$	10	10	nA
DC Current Gain	h_{FE1}	$V_{CE}=5.0 V, I_C=1.0 \mu A$	30
	h_{FE2}	$V_{CE}=5.0 V, I_C=10 \mu A$	40	120	100	500
	h_{FE3}	$V_{CE}=5.0 V, I_C=10 \mu A, TA=-55^\circ C$	10	20
	h_{FE4}	$V_{CE}=5.0 V, I_C=100 \mu A$	75	175
	h_{FE5}	$V_{CE}=5.0 V, I_C=500 \mu A$	100	200
	h_{FE6}	$V_{CE}=5.0 V, I_C=1.0 mA$	175	250
	h_{FE7}	$V_{CE}=5.0 V, I_C=10 mA \blacktriangle$	500	800
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.0 mA, I_B=0.1 mA$	0.35	0.35	volts
Base to Emitter Voltage	V_{BE}	$V_{CE}=5.0 V, I_C=0.1 mA$	0.5	0.7	0.5	0.7	volts
High Frequency Current Gain	h_{fe1}	$V_{CE}=5.0 V, I_C=0.5 mA, f=30 mc$	2.0	2.0
	h_{fe2}	$V_{CE}=5.0 V, I_C=0.05 mA, f=5.0 mc$	2.4	3.0
Collector Capacitance	C_{ob}	$V_{CB}=5.0 V, I_E=0$	6.0	6.0	pf
Input Capacitance	C_{ib}	$V_{EB}=0.5 V, I_C=0$	6.0	6.0	pf

\blacktriangle Pulse width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$